

**isc Silicon NPN Power Transistor**

**2SC2098**

**DESCRIPTION**

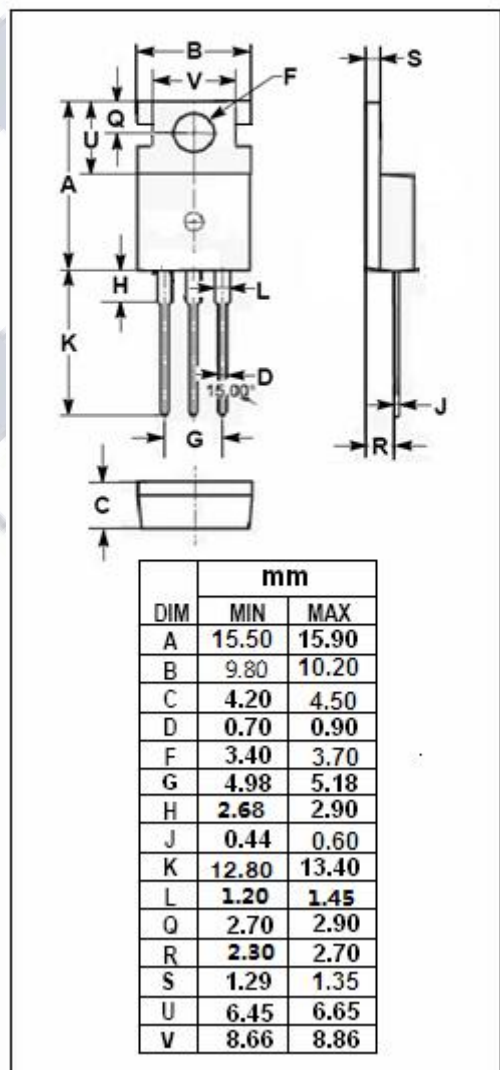
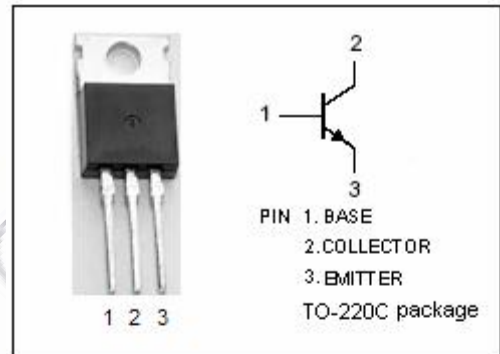
- Silicon NPN epitaxial planar
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- The 2SC2098 is designed for 25-50MHz AF power amplifier applications

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	70	V
V <sub>CEO</sub>	Collector-Emitter Voltage	70	V
V <sub>EBO</sub>	Emitter-Base Voltage	4	V
I <sub>c</sub>	Collector Current-Continuous	6	A
P <sub>c</sub>	Total Power Dissipation @ T <sub>c</sub> =25°C	25	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC2098****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=25\text{mA}; I_B=0$	70			V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=70\text{V}; I_E=0$			1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			1	mA
$h_{FE}$	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	20		100	